

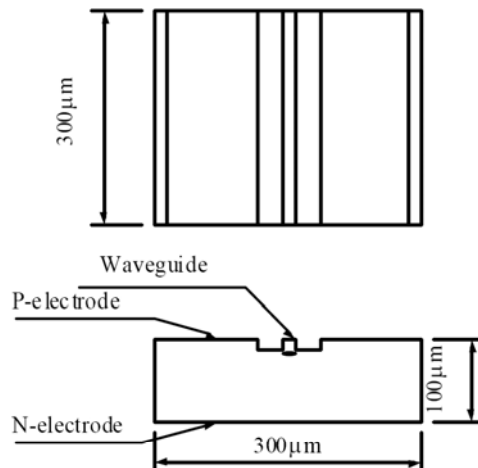


CHIP-980-P50

■ Specifications

- (1) Size : 300*300*100 μ m
- (2) Device: Laser diode bare chip
- (3) Structure Double channel , single ridge waveguide

■ External dimensions(Unit : μ m)



P-electrode and N-electrode are both gold pad.

Channel depth : 1 ~ 1.5 μ m

■ Absolute Maximum Ratings($T_c=25^{\circ}\text{C}$)

Parameter	Symbol	Rating	Unit
Optical Output	Po	50	mW
Reverse Voltage	Vr	2	V
Operating Temperature	Top	-10 ~ +40	°C
Storage Temperature	Tstg	-15 ~ +85	°C



■ Electrical and Optical Characteristics (Tc=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
Threshold Current	I _{th}	-	-	12	20	mA	
Operating Current	I _{op}	P _o =50mW	-	75	85	mA	
Operating Voltage	V _{op}	-	1	1.5	2.1	Volt	
Slope Efficiency	η	30mW-10mW	0.65	0.8	-	mW/mA	
		I _{30mW} -I _{10mW}					
Beam Divergence (FWHM)	Parallel	$\theta //$	P _o =50mW	8	13	18	deg.
	Perpendicular	$\theta \perp$	P _o =50mW	25	30	35	deg.
Lasing Wavelength	λ	P _o =50mW	970	980	995	nm	

© $\theta //$ and $\theta \perp$ are defined as the angle within which the intensity is 50% of the peak value.

© Measuring Conditions : Pulse width=5 μ s , Duty cycle=1%

SPECIFICATIONS ARE SUBJECT TO CHANGE WITHOUT NOTICE.